

Features

- High voltage rectifier
- Tandem diodes in series
- Very low switching losses
- Insulated device with internal ceramic
- Equal thermal conditions for both 300 V diodes
- Static and dynamic equilibrium of internal diodes are warranted by design
- Insulated package:
 - Insulated voltage: 2500 V_{RMS} sine

Description

This device is part of ST's second generation of 600 V tandem diodes. It has ultralow switching-losses with a minimized Q_{RR} that makes it perfect for use in circuits working in hard-switching mode. In particular the V_F/Q_{RR} trade-off positions this device between standard ultrafast diodes and silicon-carbide Schottky rectifiers in terms of price/performance ratio.

The device offers a new positioning giving more flexibility to power-circuit designers looking for good performance while still respecting cost constraints.

Featuring ST's Turbo 2 600 V technology, the device is particularly suited as a boost diode in continuous conduction mode power factor correction circuits.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	8 A
V_{RRM}	600 V
t_{rr} (typ)	13 ns
I_{RM} (typ)	2 A
V_F (typ)	2.5 V
I_{FRM}	40 A
T_j (max)	175 °C

1 Characteristics

Table 2. Absolute ratings (limiting values at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	T_j from 25 to 150 °C	600
		$T_j = -40^\circ\text{C}$	550
$I_{F(RMS)}$	Forward rms current	14	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$, square wave	$T_c = 80^\circ\text{C}$	8
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}$	55
I_{FRM}	Repetitive peak forward current	$T_c = 80^\circ\text{C}, \delta = 0.1$	40
T_{stg}	Storage temperature range	-65 to +175	°C
T_j	Operating junction temperature range	-40 to +175	°C

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.9	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	-		6	μA
		$T_j = 125^\circ\text{C}$		-	20	200	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8 \text{ A}$	-	3.4		V
		$T_j = 150^\circ\text{C}$		-	2.5	3.1	

1. Pulse test: $t_p = 5 \text{ ms}$, $\delta < 2\%$ 2. Pulse test: $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 2.2 \times I_{F(AV)} + 0.113 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ\text{C}$	$I_F = 1 \text{ A}, V_R = 30 \text{ V},$ $dI_F/dt = -50 \text{ A}/\mu\text{s}$	-	20	26	ns
			$I_F = 8 \text{ A}, V_R = 400 \text{ V},$ $dI_F/dt = -200 \text{ A}/\mu\text{s}$	-	13	17	
I_{RM}	Reverse recovery current	$T_j = 125^\circ\text{C}$	$I_F = 8 \text{ A}, V_R = 400 \text{ V},$ $dI_F/dt = -200 \text{ A}/\mu\text{s}$	-	2	2.6	A
S	Softness factor			-	0.9	-	-
Q_{RR}	Reverse recovery charge	$T_j = 25^\circ\text{C}$	$I_F = 8 \text{ A}, V_R = 400 \text{ V},$ $dI_F/dt = -200 \text{ A}/\mu\text{s}$	-	4	-	nC
		$T_j = 125^\circ\text{C}$		-	20	-	-

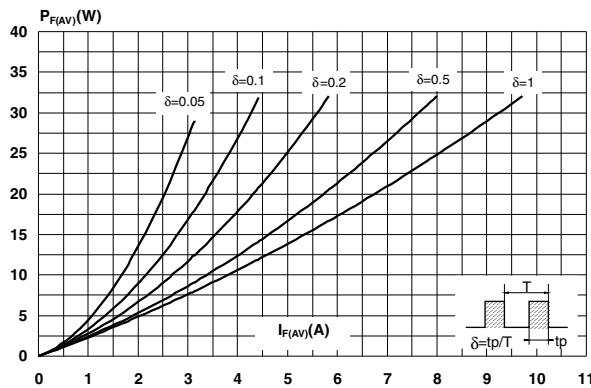
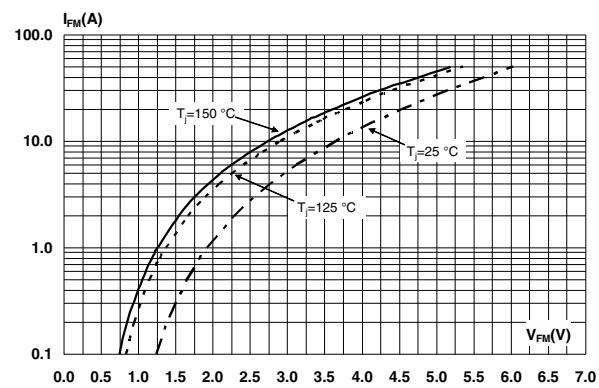
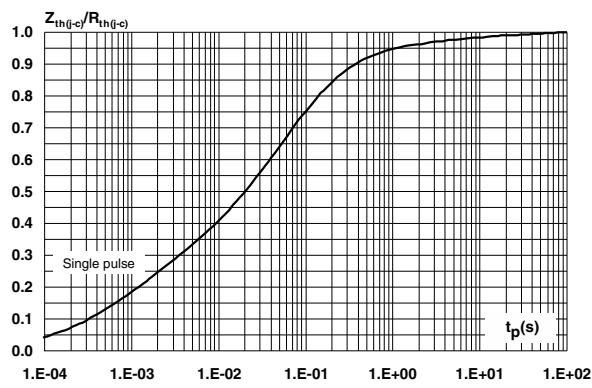
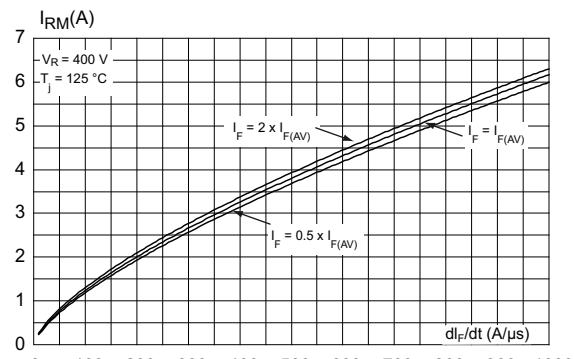
Figure 1. Average forward power dissipation versus average forward current**Figure 2. Forward voltage drop versus forward current (typical values)****Figure 3. Relative variation of thermal impedance, junction to case, versus pulse duration****Figure 4. Peak reverse recovery current versus dI_F/dt (typical values)**

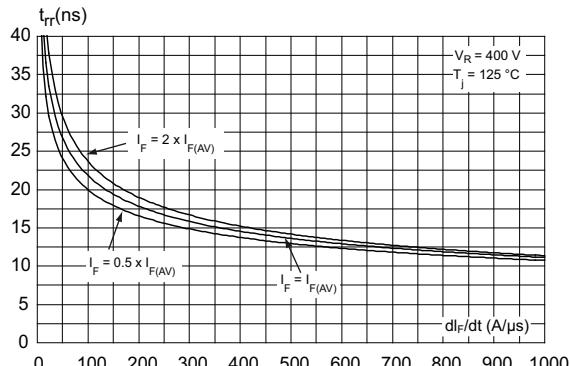
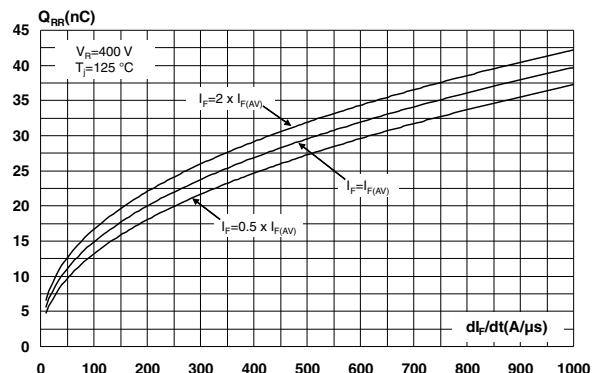
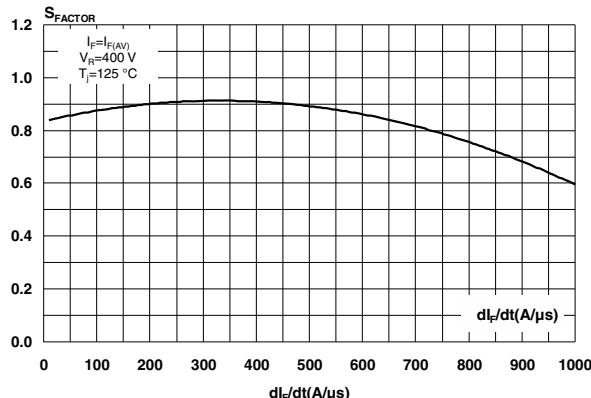
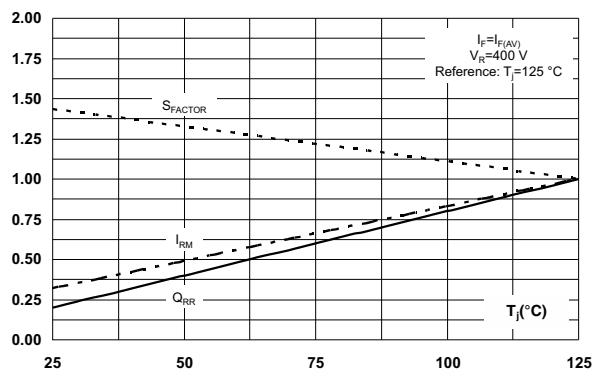
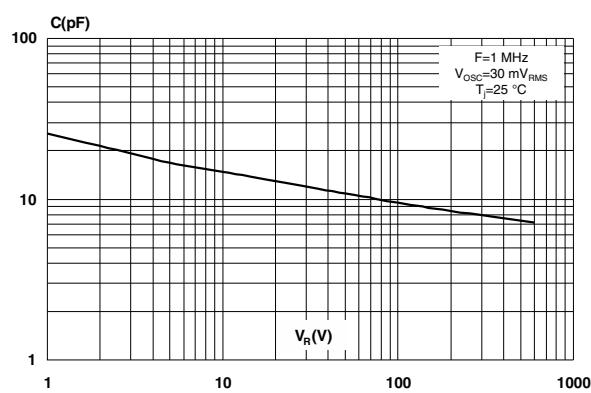
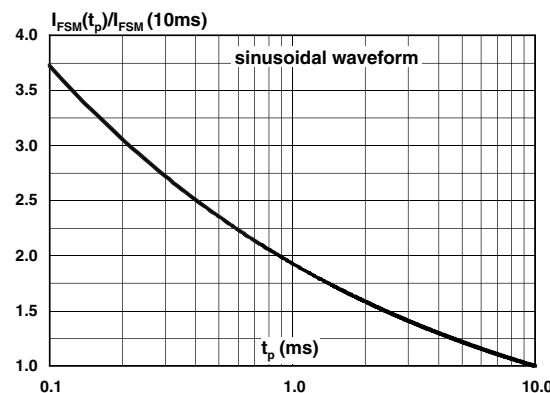
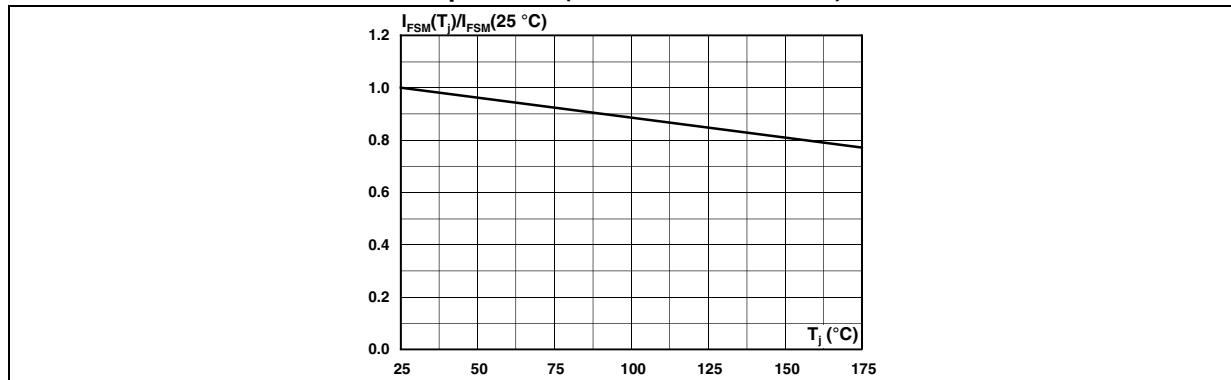
Figure 5. Reverse recovery time versus dI_F/dt (typical values)**Figure 6. Reverse recovery charges versus dI_F/dt (typical values)****Figure 7. Reverse recovery softness factor versus dI_F/dt (typical values)****Figure 8. Relative variations of dynamic parameters versus junction temperature****Figure 9. Junction capacitance versus reverse voltage applied (typical values)****Figure 10. Relative variation of non-repetitive peak surge forward current versus pulse duration**

Figure 11. Relative variation of non-repetitive peak surge forward current versus initial junction temperature (sinusoidal waveform)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque: 0.55 N·m
- Maximum torque: 0.7 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
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2.1 TO-220AC ins. package information

Figure 12. TO-220AC ins. package outline

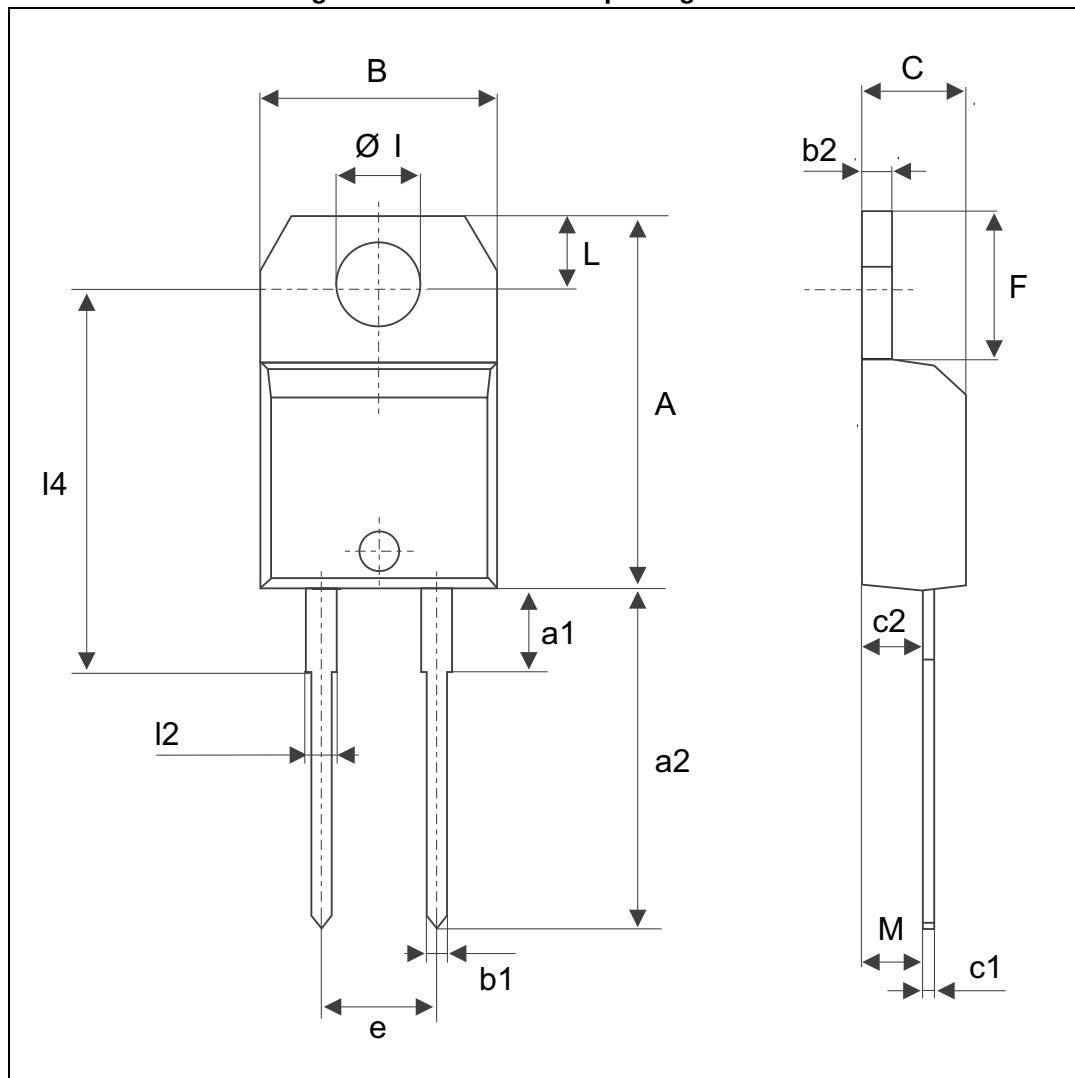


Table 6. T0-220AC ins. package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	4.80		5.40	0.189		0.212
F	6.20		6.60	0.244		0.259
Øl	3.75		3.85	0.147		0.151
l4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
l2	1.14		1.70	0.044		0.066
M		2.60			0.102	

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH8ST06DI	STTH8ST06DI	TO-220AC ins	2.3 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
14-May-2013	1	Initial release
27-Jul-2015	2	Updated <i>Features</i> , <i>Table 2</i> , <i>Table 7</i> , <i>Figure 4</i> and torque value.

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